

# High Voltage Power MOSFET

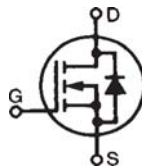
## IXTF02N450

$$V_{DSS} = 4500V$$

$$I_{D25} = 200mA$$

$$R_{DS(on)} \leq 625\Omega$$

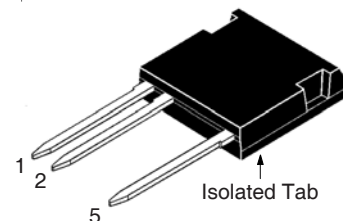
(Electrically Isolated Tab)



N-Channel Enhancement Mode

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	4500	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	4500	V
$V_{GSS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ C$	200	mA
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	600	mA
$P_D$	$T_C = 25^\circ C$	78	W
$T_J$		- 55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		- 55 ... +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	Plastic Body for 10s	260	$^\circ C$
$F_C$	Mounting Force	20..120 / 4.5..27	N/lb.
$V_{ISOL}$	50/60Hz, 1 Minute	4500	V~
<b>Weight</b>		6	g

ISOPLUS i4-Pak™



1 = Gate      5 = Drain  
2 = Source

### Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 4500V~ Electrical Isolation
- Molding Epoxies meet UL 94 V-0 Flammability Classification

### Advantages

- High Voltage Package
- Easy to Mount
- Space Savings
- High Power Density

### Applications

- High Voltage Power Supplies
- Capacitor Discharge Applications
- Pulse Circuits
- Laser and X-Ray Generation Systems

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	4.0		6.5 V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = 3.6kV$ , $V_{GS} = 0V$			5 $\mu A$
	$V_{DS} = 4.5kV$			10 $\mu A$
	$V_{DS} = 3.6kV$ Note 2, $T_J = 125^\circ C$		15	$\mu A$
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 10mA$ , Note 1			625 $\Omega$

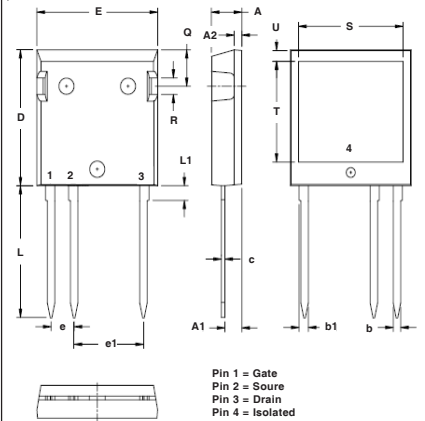
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 50\text{V}$ , $I_D = 50\text{mA}$ , Note 1	90	150	mS
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		246	pF
$C_{oss}$			19	pF
$C_{rss}$			5.8	pF
$R_{Gi}$	Gate Input Resistance		76	$\Omega$
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 500\text{V}$ , $I_D = 0.5 \cdot I_{D25}$ $R_G = 10\Omega$ (External)		17	ns
$t_r$			48	ns
$t_{d(off)}$			28	ns
$t_f$			143	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 1\text{kV}$ , $I_D = 0.5 \cdot I_{D25}$		10.6	nC
$Q_{gs}$			3.3	nC
$Q_{gd}$			5.5	nC
$R_{thJC}$				1.6 $^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_s$	$V_{GS} = 0\text{V}$			200 mA
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			800 mA
$V_{SD}$	$I_F = I_s$ , $V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 200\text{mA}$ , $-di/dt = 50\text{A}/\mu\text{s}$ , $V_R = 100\text{V}$		1.6	$\mu\text{s}$

- Notes: 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .  
2. Part must be heatsunk for high-temp  $I_{DSS}$  measurement.

### ISOPLUS i4-Pak™ (HV) Outline



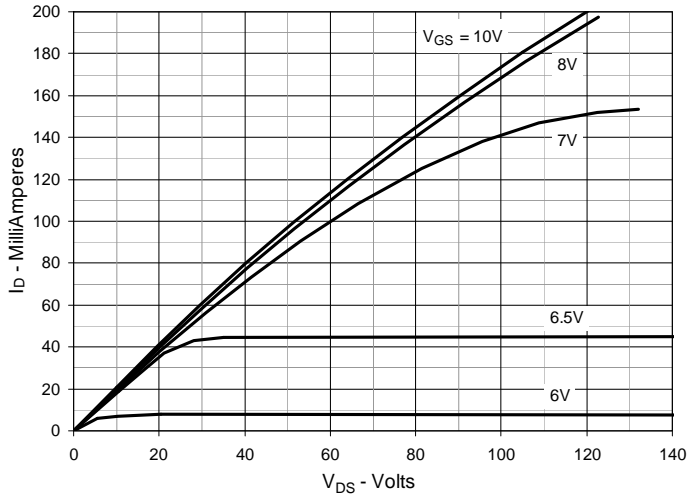
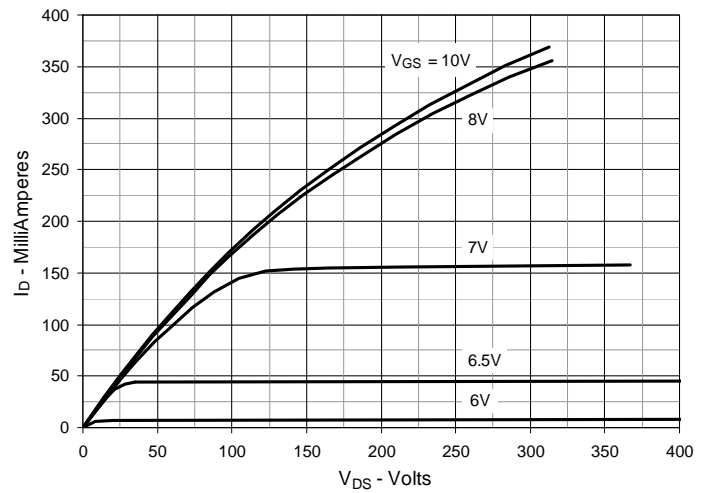
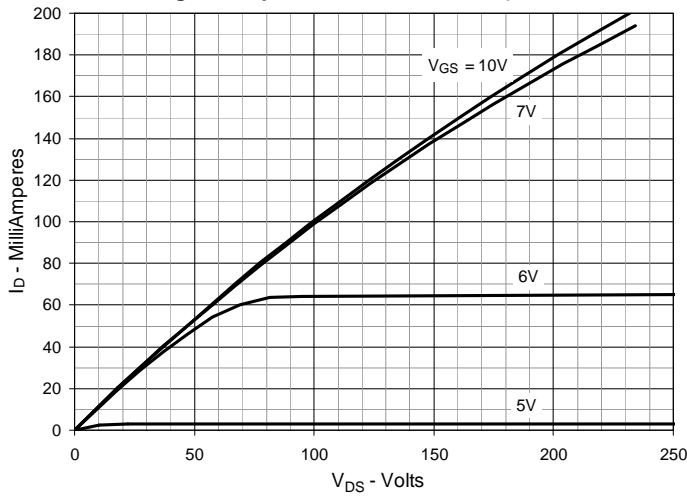
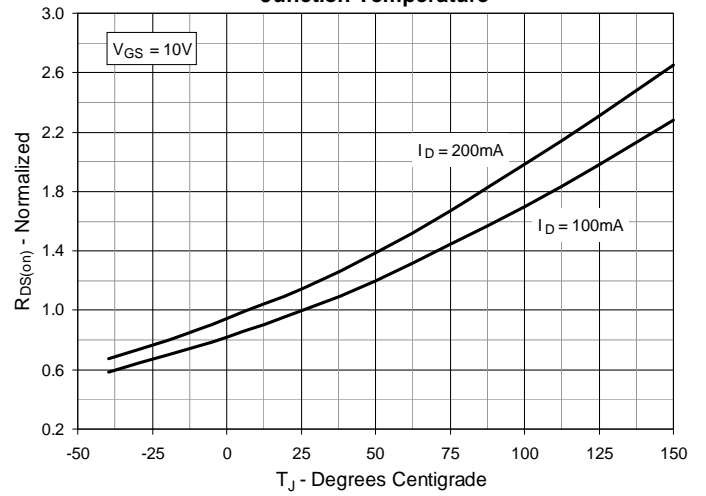
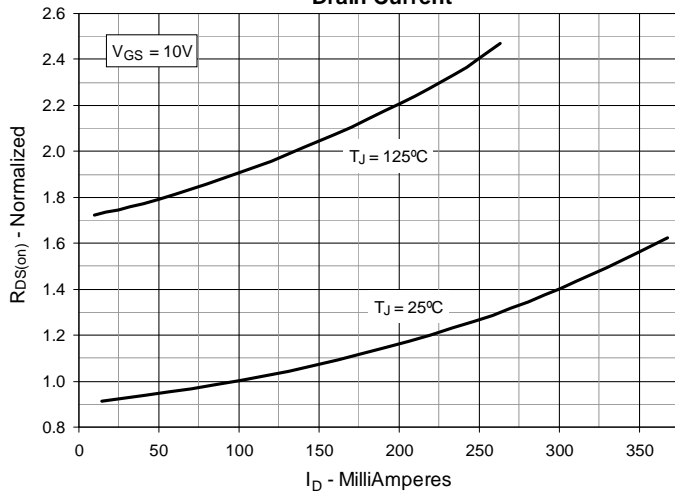
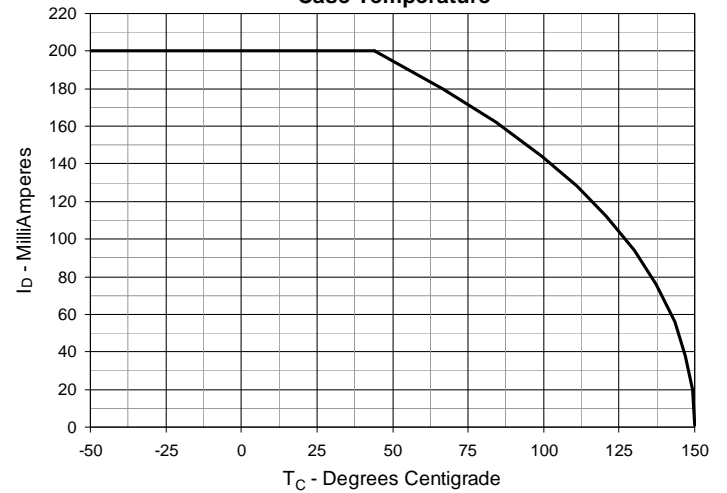
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.102	.118	2.59	3.00
A2	.046	.085	1.17	2.16
b	.045	.055	1.14	1.40
b1	.058	.068	1.47	1.73
C	.020	.029	0.51	0.74
D	.819	.840	20.80	21.34
E	.770	.799	19.56	20.29
e	.150 BSC		3.81 BSC	
e1	.450 BSC		11.43 BSC	
L	.780	.840	19.81	21.34
L1	.083	.102	2.11	2.59
Q	.210	.244	5.33	6.20
R	.100	.180	2.54	4.57
S	.660	.690	16.76	17.53
T	.590	.620	14.99	15.75
U	.065	.080	1.65	2.03

### PRELIMINARY TECHNICAL INFORMATION

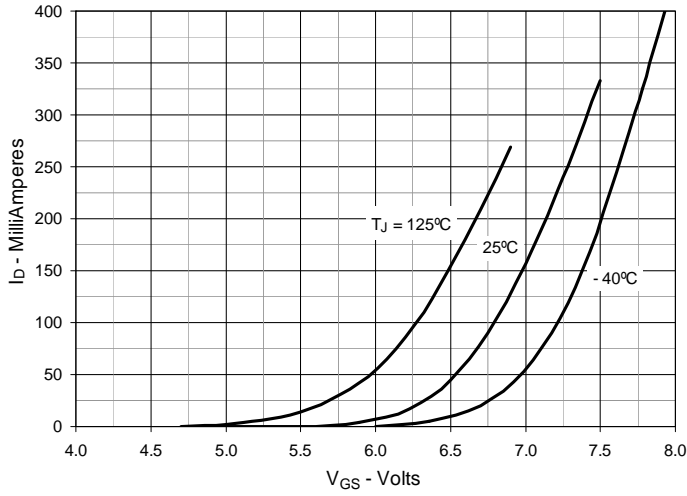
The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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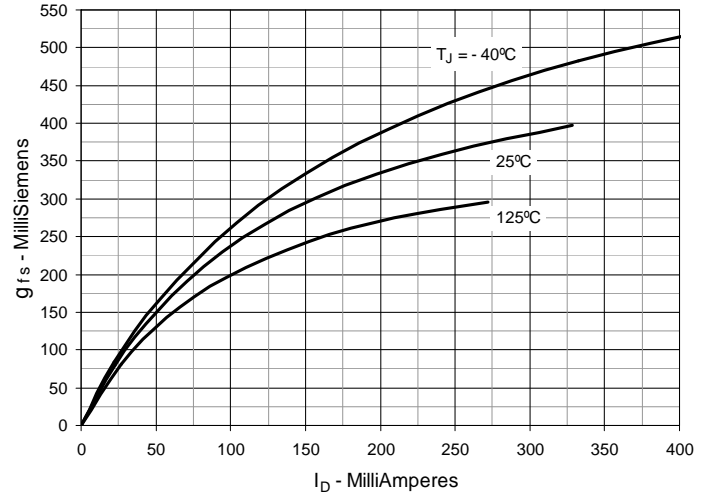
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$** 

**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 100\text{mA}$  Value vs. Junction Temperature**

**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 100\text{mA}$  Value vs. Drain Current**

**Fig. 6. Maximum Drain Current vs. Case Temperature**


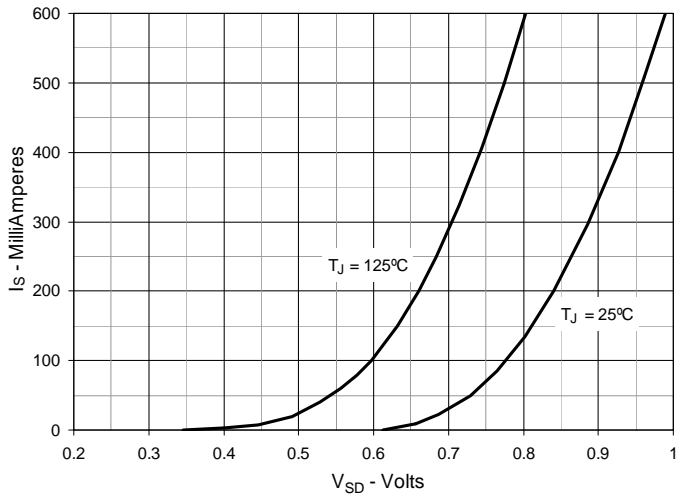
**Fig. 7. Input Admittance**



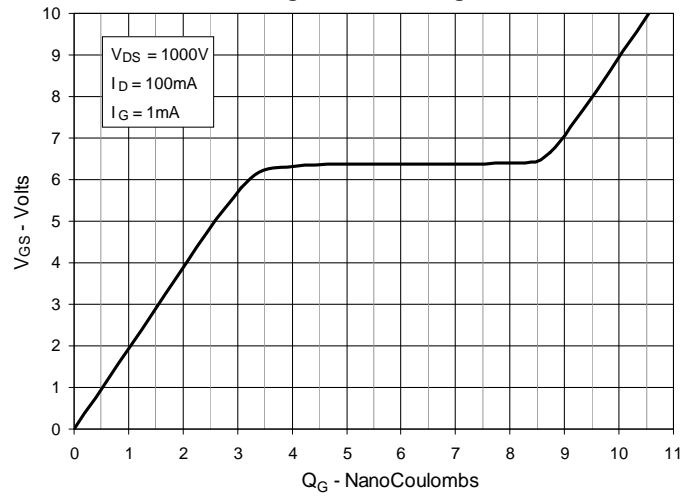
**Fig. 8. Transconductance**



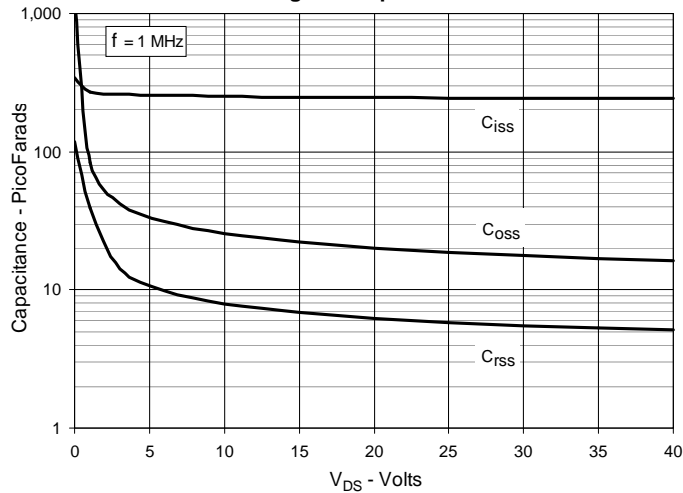
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



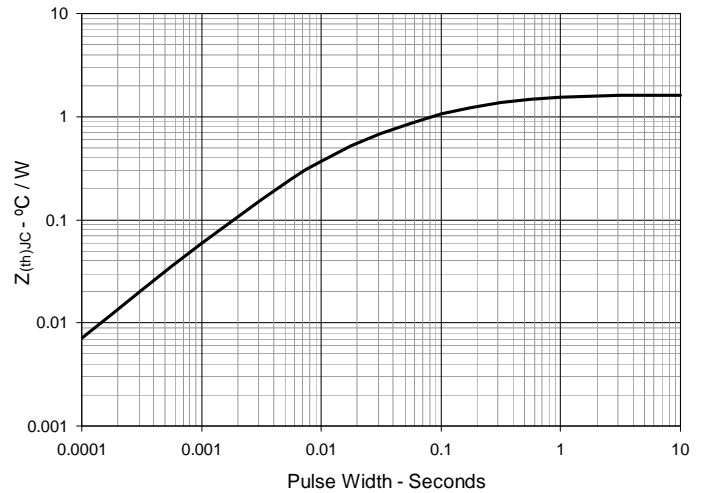
**Fig. 10. Gate Charge**



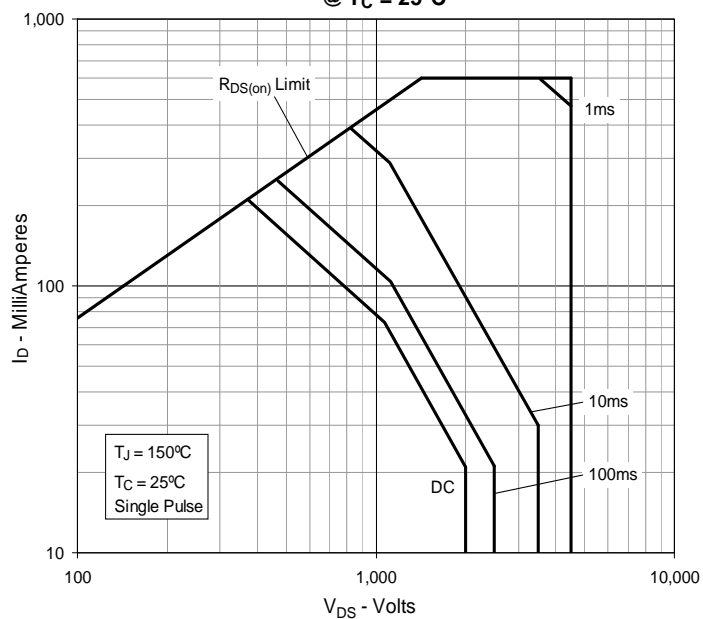
**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Impedance**



**Fig. 13. Forward-Bias Safe Operating Area**  
@  $T_C = 25^\circ\text{C}$



**Fig. 14. Forward-Bias Safe Operating Area**  
@  $T_C = 75^\circ\text{C}$

